TOSHIBA Transistor Silicon NPN Epitaxial Type (PCT process)

2SC2883

Audio Frequency Amplifier Applications

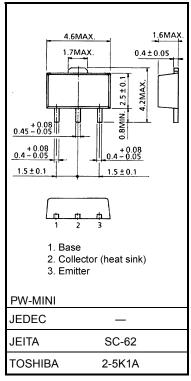
- Suitable for output stage of 3 watts amplifier
- Small flat package
- PC = 1.0 to 2.0 W (mounted on a ceramic substrate)
- Complementary to 2SA1203

Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Rating	Unit	
Collector-base voltage	V_{CBO}	30	V	
Collector-emitter voltage	V _{CEO}	30	٧	
Emitter-base voltage	V _{EBO}	5	٧	
Collector current	IC	1.5	Α	
Base current	ΙΒ	0.3	Α	
Collector power dissipation	PC	500	mW	
	P _C (Note 1)	1000		
Junction temperature	Tj	150	°C	
Storage temperature range	T _{stg}	-55 to 150	°C	

Note 1: Mounted on a ceramic substrate (250 $\text{mm}^2 \times 0.8 \text{ t}$)

Unit: mm



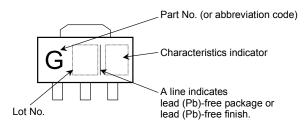
Weight: 0.05 g (typ.)

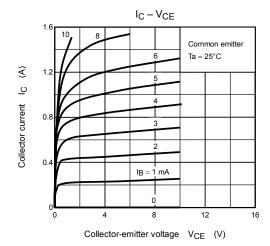
Electrical Characteristics (Ta = 25°C)

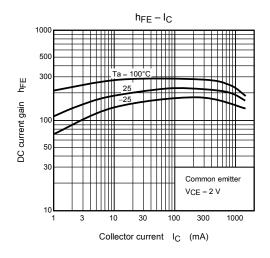
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Collector cut-off current	I _{CBO}	V _{CB} = 30 V, I _E = 0	_	_	0.1	μA
Emitter cut-off current	I _{EBO}	V _{EB} = 5 V, I _C = 0	_	_	0.1	μA
Collector-emitter breakdown voltage	V (BR) CEO	I _C = 10 mA, I _B = 0	30	_	_	٧
Emitter-base breakdown voltage	V (BR) EBO	I _E = 1 mA, I _C = 0	5	_	_	٧
DC current gain	h _{FE} (Note 2)	V _{CE} = 2 V, I _C = 500 mA	100	_	320	_
Collector-emitter saturation voltage	V _{CE (sat)}	I _C = 1.5 A, I _B = 0.03 A	_	_	2.0	V
Base-emitter voltage	V _{BE}	V _{CE} = 2 V, I _C = 500 mA	_	_	1.0	٧
Transition frequency	f _T	V _{CE} = 2 V, I _C = 500 mA	_	120	_	MHz
Collector output capacitance	C _{ob}	V _{CB} = 10 V, I _E = 0, f = 1 MHz	_	_	40	pF

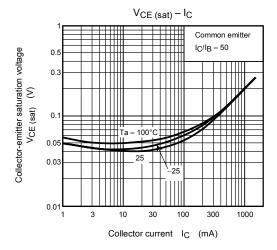
Note 2: hFE classification O: 100 to 200, Y: 160 to 320

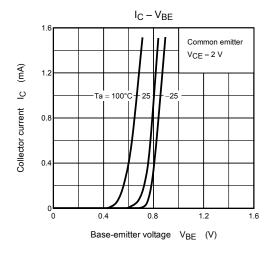
Marking

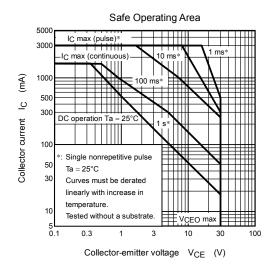


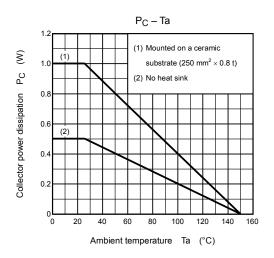












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